

X0008

N-Channel Enhancement Mode MOSFET

30V(VDS) / $\pm 12\text{V}$ (VGS) / 5.8A(ID)

Rev1.7



Wafer Specification

1. Order Information

Part No.	Description	Gross die / per 8" wafer
X0008	30V(V_{DS}) / $\pm 12V(V_{GS})$ / 5.8A(I_D) N-Channel Enhancement Mode MOSFET	55,496

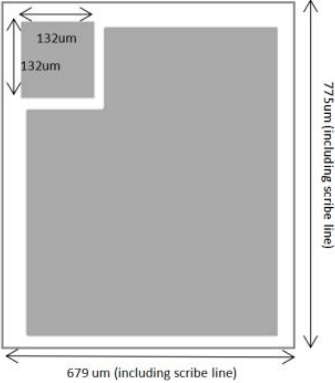
2. Mechanical Data

Nominal Back Metal Composition, Thickness	Ti-Ni-Ag (13kÅ°)
Nominal Front Metal Composition, Thickness	AlCu (4µm)
Wafer Diameter	200mm, with Ø10 notch
Wafer Thickness	150±10µm
Scribe Line Width	60µm
Passivation	SiN+SiO ₂

3. Key Electrical Characteristics of Die (at T_J = 25 °C, unless otherwise specified)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30			V	$V_{GS}=0V$, $I_D=250\mu A$
I_D (Device Ref)	Continuous Drain Current			5.8	A	$T_J=25^\circ C$
$R_{DS(on)}(CP)$	Static Drain-to-Source On-Resistance		20	27	mΩ	$V_{GS}=10V$, $I_D=1A$
			22	30	mΩ	$V_{GS}=4.5V$, $I_D=1A$
			29	50	mΩ	$V_{GS}=2.5V$, $I_D=1A$
$R_{DS(on)}(FT)$	Static Drain-to-Source On-Resistance		25	32	mΩ	$V_{GS}=10V$, $I_D=5.8A$
			28	34	mΩ	$V_{GS}=4.5V$, $I_D=5A$
			36	54	mΩ	$V_{GS}=2.5V$, $I_D=3A$
$V_{GS(th)}$	Gate Threshold Voltage	0.6	0.95	1.3	V	$V_{DS}=V_{GS}$, $I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			1	µA	$V_{DS}=30V$, $V_{GS}=0V$
I_{GSS}	Gate-to-Source Leakage Current			±100	nA	$V_{GS}=\pm 12V$, $V_{DS}=0V$
T_J , T_{STG}	Operating and Storage Temperature	-55°C to 150°C Max				

4. Die Outline & FT Data

	Die Size: 775µm × 679µm (including scribe line)
	Gate: 132µm × 132µm
	For SOT23-3 package Suggest Bonding wire: Gate: 1 × 1.0 mil Cu Source: 6 × 1.65 mil Cu